

HTT1127E

Silicon NPN Epitaxial Twin Transistor

REJ03G0839-0100
 (Previous ADE-208-1540)
 Rev.1.00
 Aug.10.2005

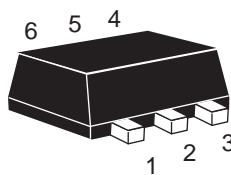
Features

- Include 2 transistors in a small size SMD package: EMFPAK-6 (6 Leads: 1.2 x 0.8 x 0.5 mm)

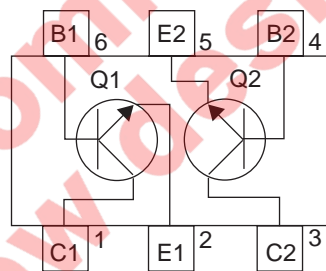
Q1: Equivalent Buffer transistor	Q2: Equivalent OSC transistor
2SC5700	2SC5849

Outline

RENESAS Package code: PXSF0006LA-A
 (Package name: EMFPAK-6)



Pin Arrangement



1. Collector Q1
2. Emitter Q1
3. Collector Q2
4. Base Q2
5. Emitter Q2
6. Base Q1

Note: Marking is "R".

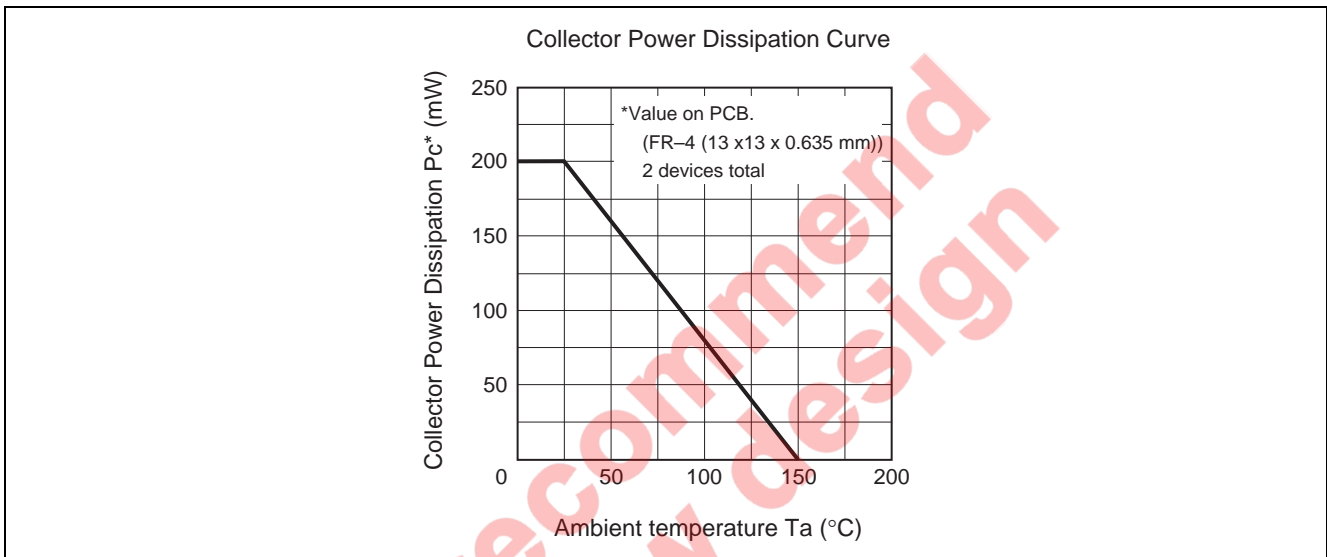
Not recommended for new design

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings		Unit
		Q1	Q2	
Collector to base voltage	V _{CBO}	15	15	V
Collector to emitter voltage	V _{CEO}	4	6	V
Emitter to base voltage	V _{EBO}	1.5	1.5	V
Collector current	I _C	50	80	mA
Collector power dissipation	P _C	Total 200*		mW
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-50 to +150	°C

Note: *Value on PCB. (FR-4 (13 x 13 x 0.635 mm)).



Q1 Electrical Characteristics

(Ta = 25°C)

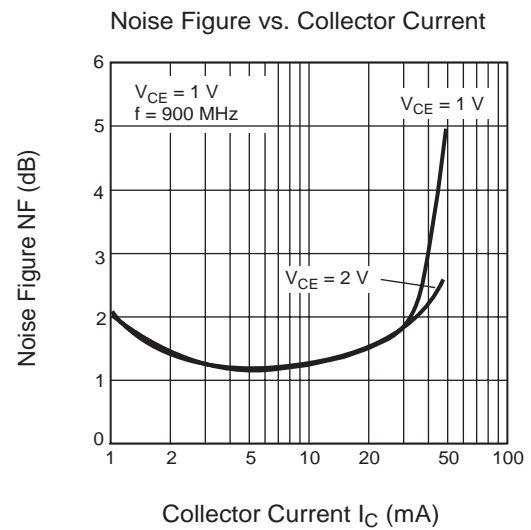
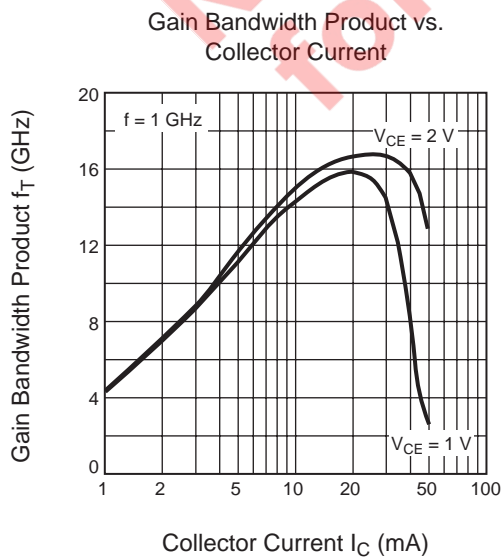
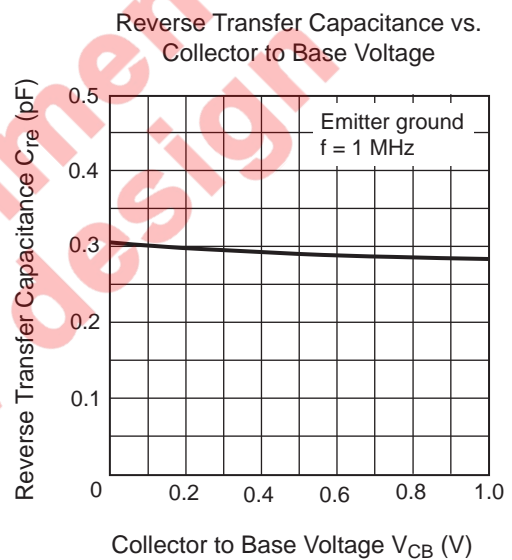
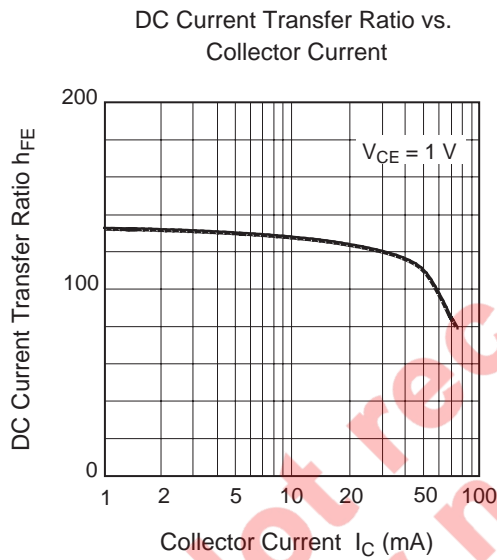
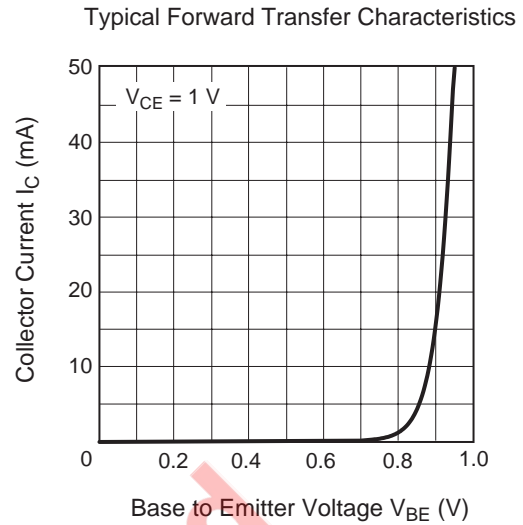
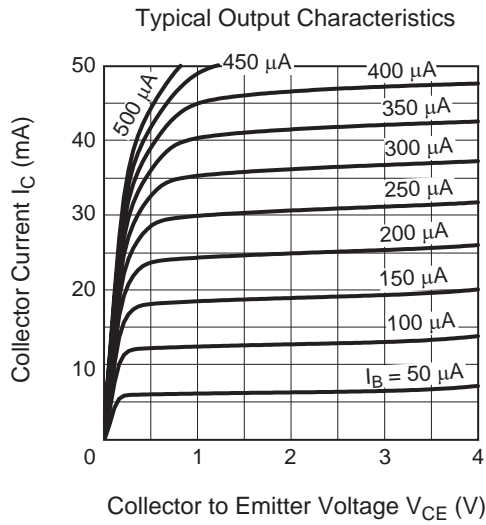
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 15 V, I_E = 0$
Collector cutoff current	I_{CEO}	—	—	1.0	μA	$V_{CE} = 4 V, R_{BE} = \text{infinite}$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 0.8 V, I_C = 0$
DC current transfer ratio	h_{FE}	100	120	150	—	$V_{CE} = 1 V, I_C = 5 mA$
Reverse transfer capacitance	C_{re}	—	0.3	0.45	pF	$V_{CB} = 1 V, f = 1 MHz$ Emitter ground
Gain bandwidth product	f_T	10	12	—	GHz	$V_{CE} = 1 V, I_C = 5 mA,$ $f = 1 GHz$
Forward transfer coefficient	$ S_{21} ^2$	13	16	—	dB	$V_{CE} = 1 V, I_C = 5 mA,$
Noise figure	NF	—	1.0	1.7	dB	$f = 900 MHz,$ $\Gamma_S = \Gamma_L = 50 \Omega$

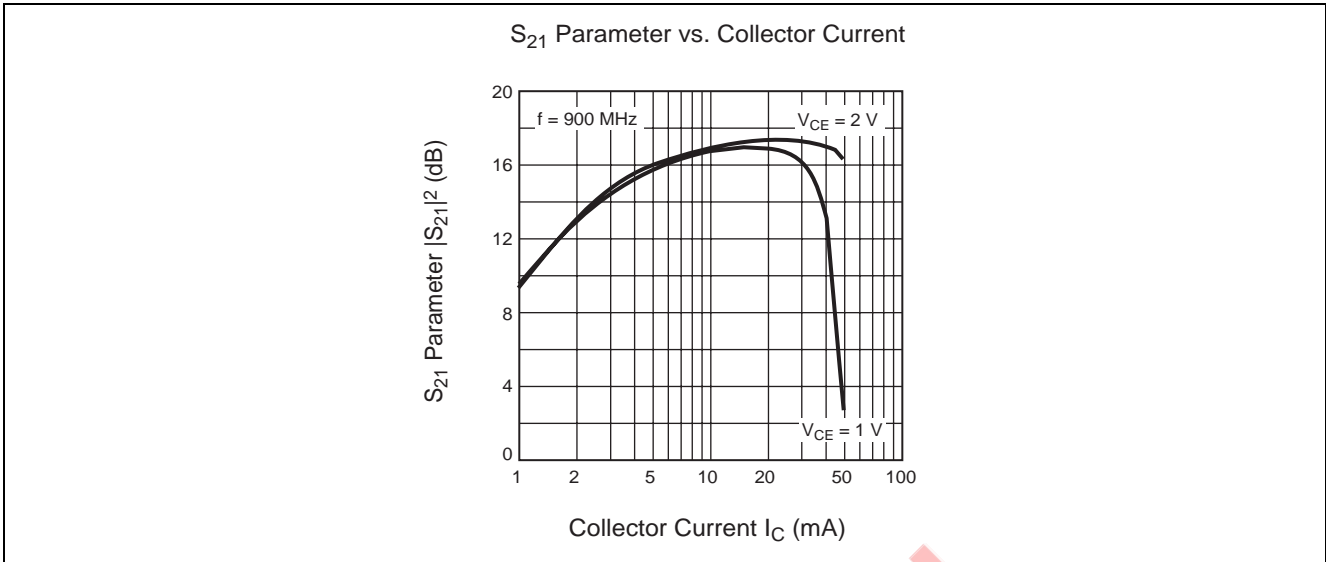
Q2 Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 15 V, I_E = 0$
Collector cutoff current	I_{CEO}	—	—	0.1	μA	$V_{CE} = 4 V, R_{BE} = \text{infinite}$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	h_{FE}	90	120	140	—	$V_{CE} = 1 V, I_C = 5 mA$
Reverse transfer capacitance	C_{re}	—	0.50	0.65	pF	$V_{CB} = 1 V, f = 1 MHz$ Emitter ground
Gain bandwidth product	f_T	2.0	4.0	—	GHz	$V_{CE} = 1 V, I_C = 5 mA,$ $f = 1 GHz$
Forward transfer coefficient	$ S_{21} ^2$	7	11	—	dB	$V_{CE} = 1 V, I_C = 5 mA,$
Noise figure	NF	—	1.7	2.3	dB	$f = 900 MHz$ $\Gamma_S = \Gamma_L = 50 \Omega$

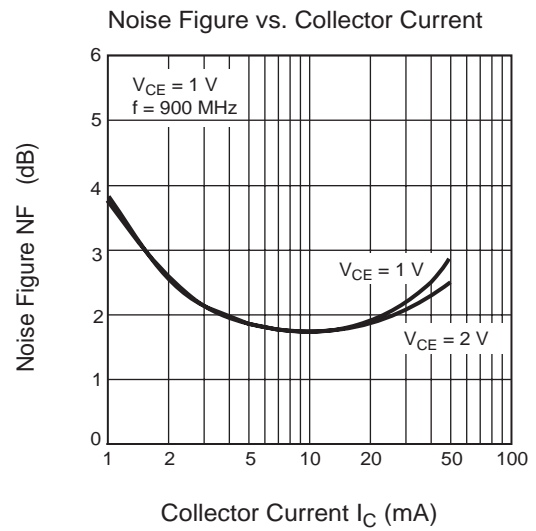
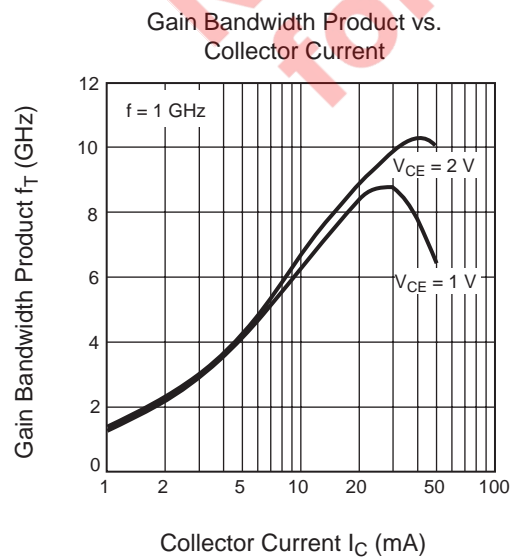
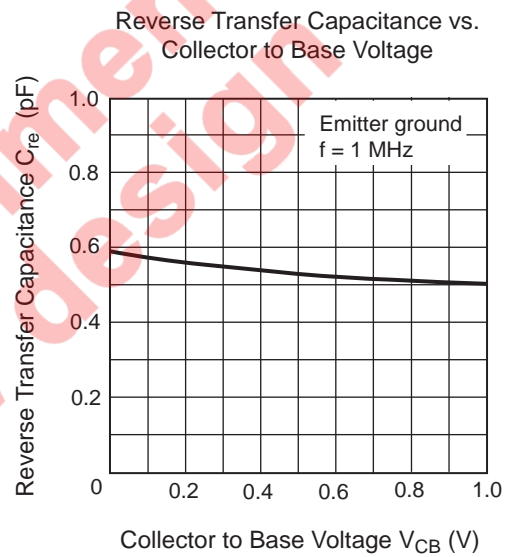
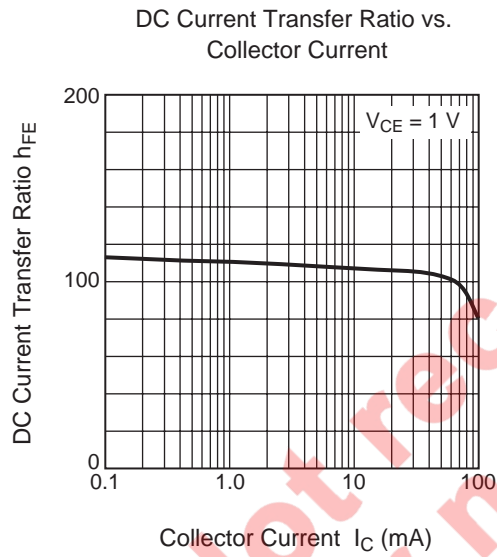
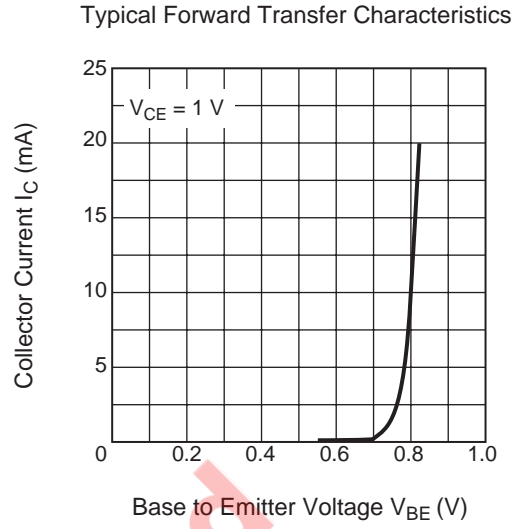
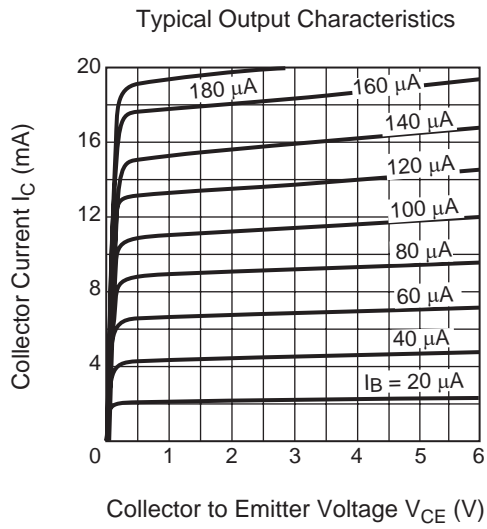
Q1 Main Characteristics

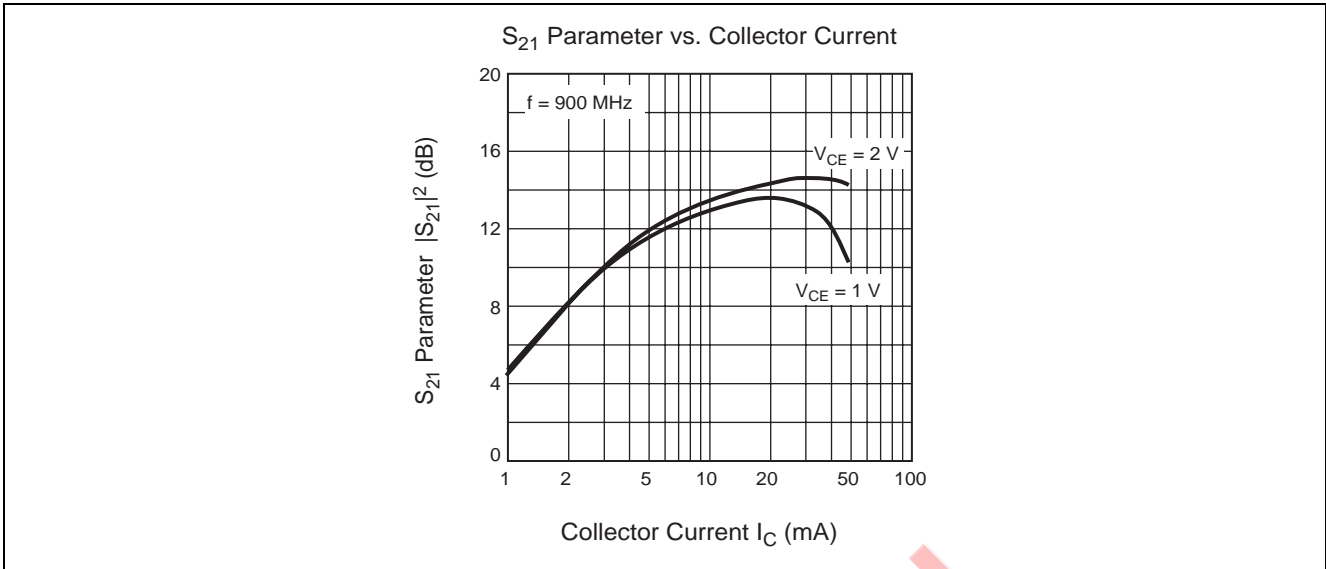




Not recommended for new design

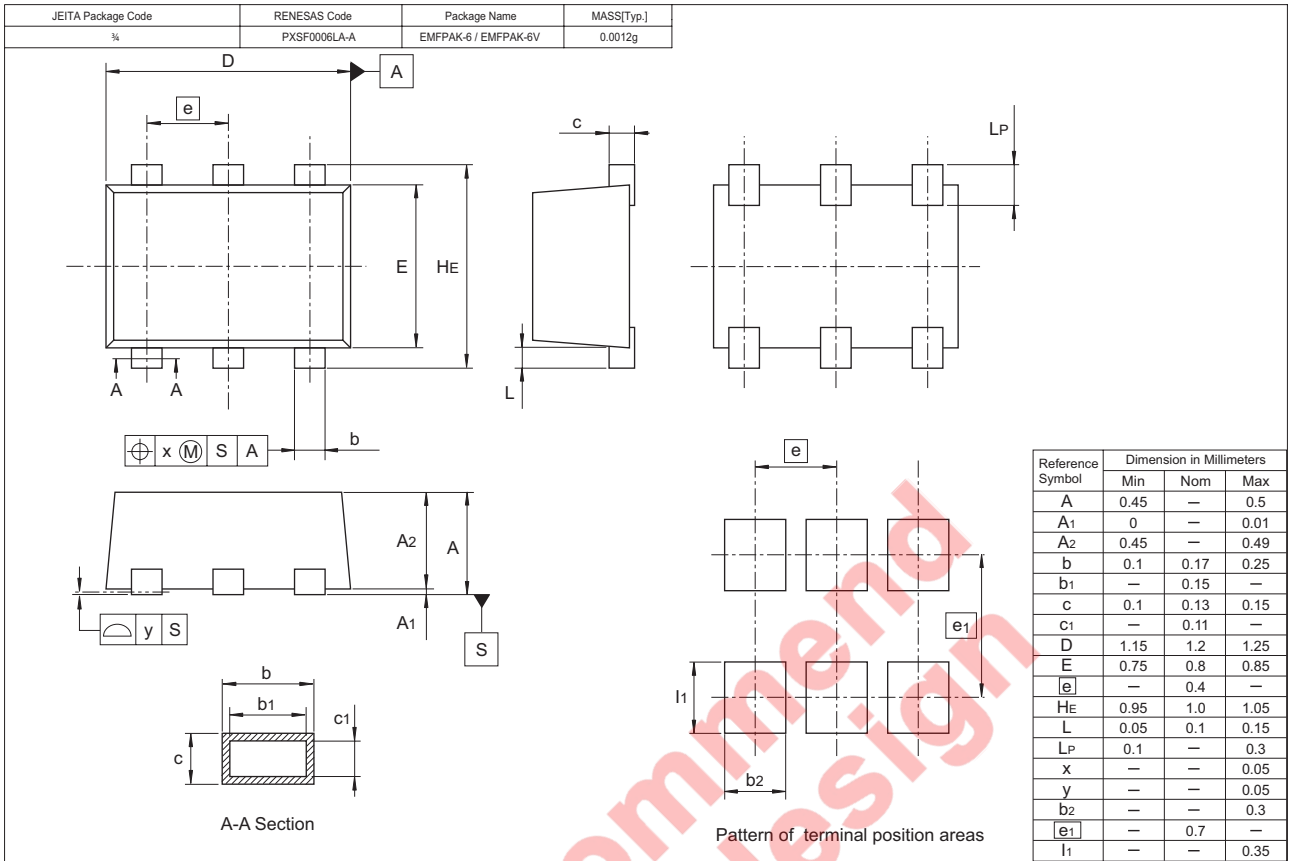
Q2 Main Characteristics





Not recommended
for new design

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HTT1127ERTL-E	5000	φ 178 mm Reel, 8 mm Emboss Taping

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